Description

JMT N-channel MOSFET

Features

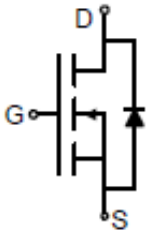
- V_{DS}=20V, I_D=4A
- $R_{DS(ON)}$ <59 mΩ @ V_{GS} = 2.5V
  $R_{DS(ON}$ <45mΩ @ V_{GS} = 4.5V
- High Power and Current Handing Capability
- Lead Free Product is Acquired
- Surface Mount Package

Application

- Battery Protection
- Load Switch
- Power Management

Package

SOT-23



Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25℃	4	A
		T_C = 100℃	2.5	
I_{DM}	Pulsed Drain Current note1		10	A
P_D	Power Dissipation	T_C = 25℃	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		125	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= 250μA	20	22	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =20V, V_{GS} = 0V,	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= 250μA	0.5	0.85	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =2.5V, I_D =2.5A	-	37	59	mΩ
		V_{GS} =4.5V, I_D =2.9A	-	30	45	
g_{FS}	Forward Transconductance	V_{DS} =5V, I_D =2.9A	-	8	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz	-	300	-	pF
C_{oss}	Output Capacitance		-	120	-	pF
C_{rss}	Reverse Transfer Capacitance		-	80	-	pF
Q_g	Total Gate Charge	V_{DS} = 10V, I_D = 2.9A, V_{GS} = 4.5V	-	4.0	10	nC
Q_{gs}	Gate-Source Charge		-	0.65	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	1.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 10V, I_D =2.9A, R_{GEN} = 6Ω, V_{GS}=4.5V,	-	10	15	ns
t_r	Turn-on Rise Time		-	50	85	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	45	ns
t_f	Turn-off Fall Time		-	10	20	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	10	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S =2.9A	-	0.75	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

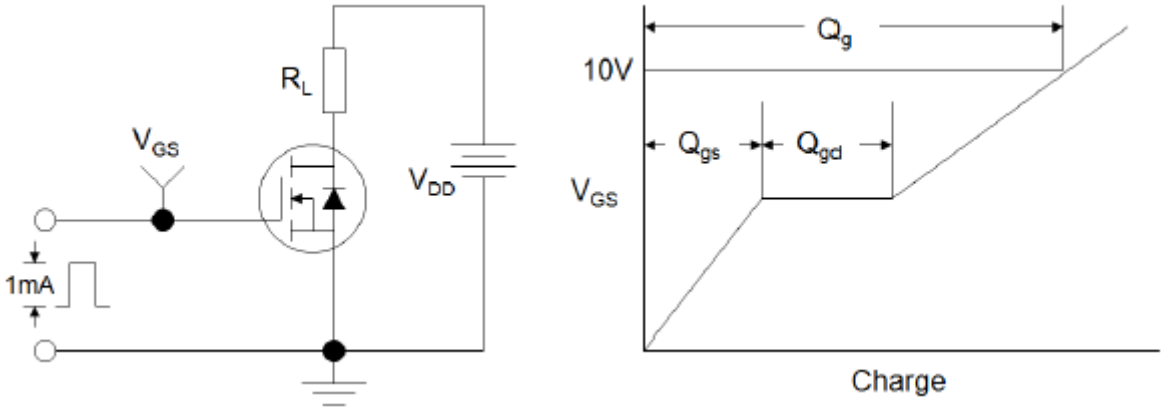


Figure1:Gate Charge Test Circuit & Waveform

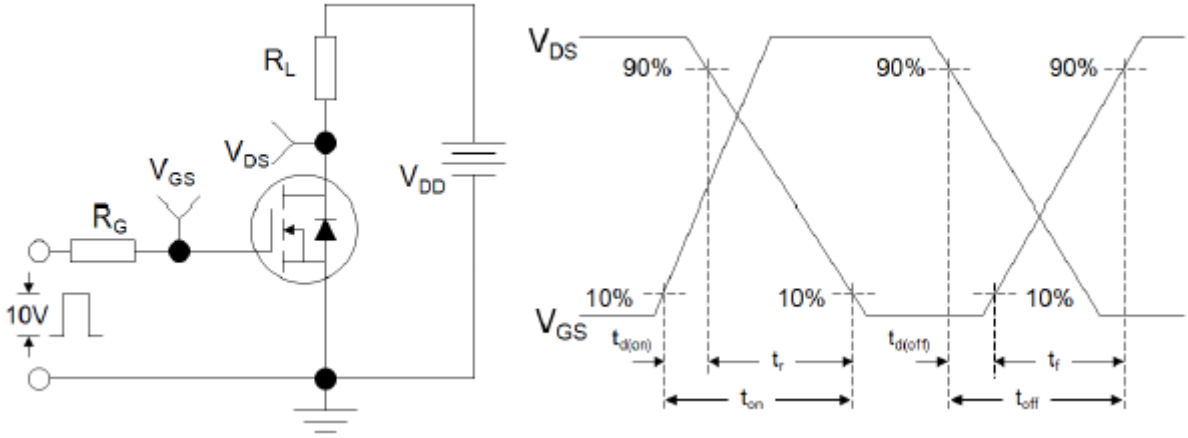


Figure 2: Resistive Switching Test Circuit & Waveforms

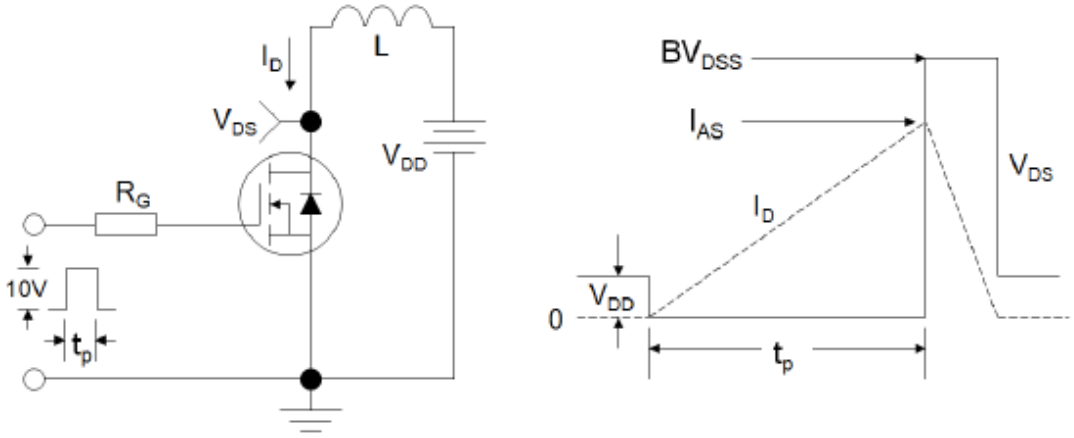


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

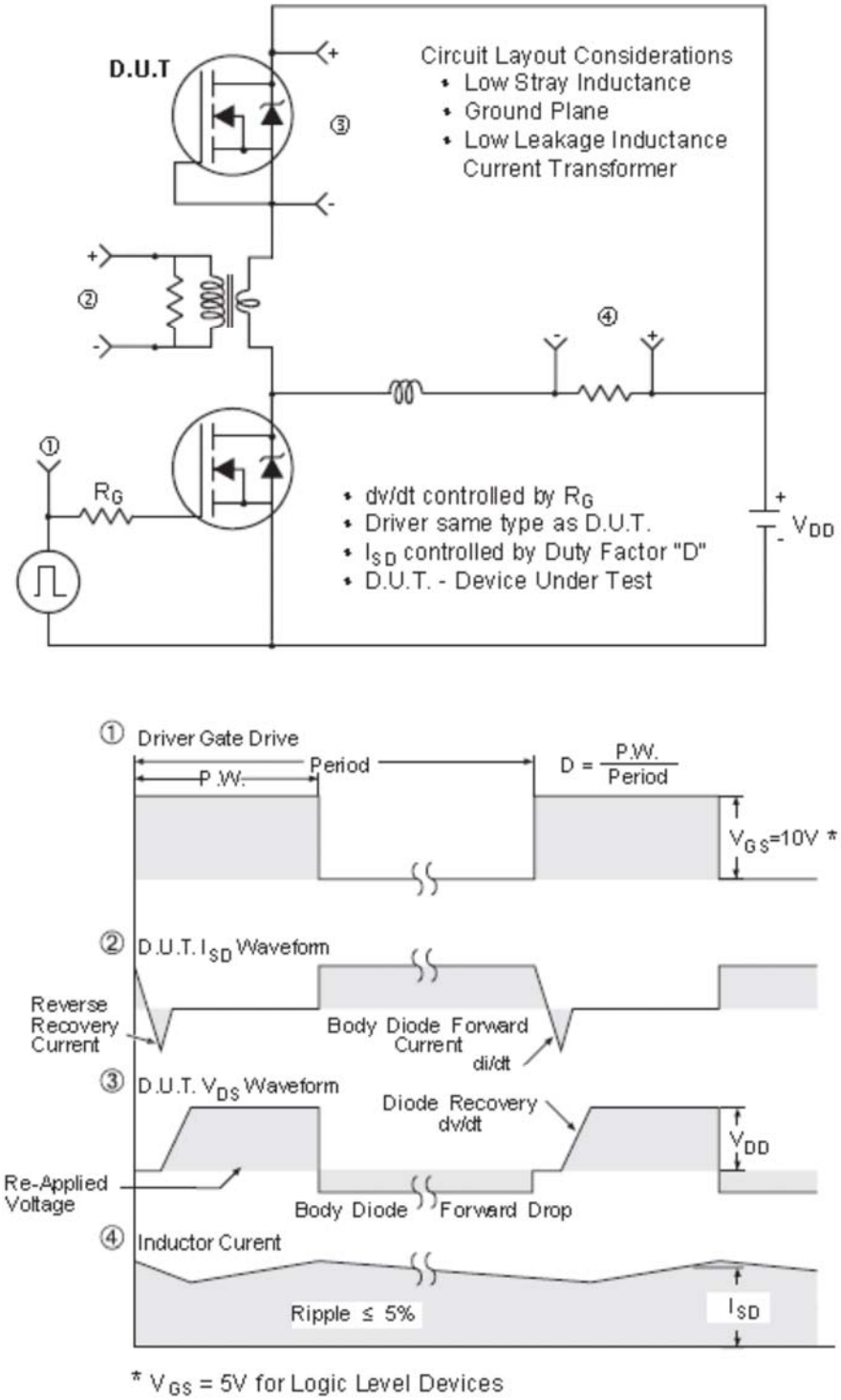
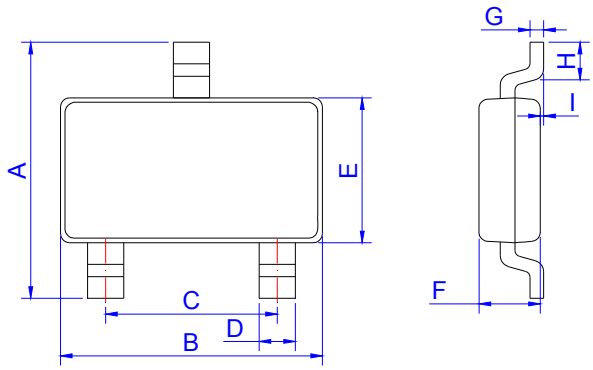


Figure 4:Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

Package Mechanical Data



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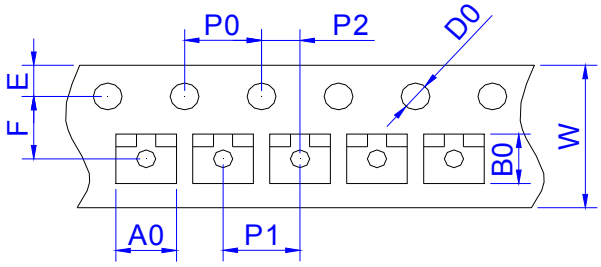
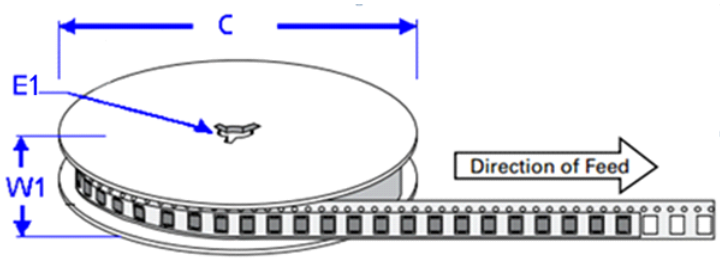
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Package Information-SOT-23





Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

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